



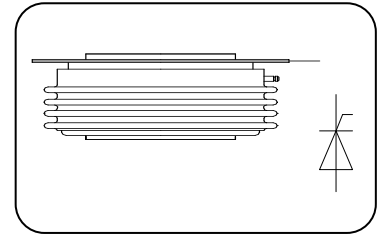
**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Inductive heating
- Electronic welders
- Self-commutated inverters

**$I_{T(AV)}$  4000A**  
 **$V_{DRM}/V_{RRM}$  2200~3000V**  
 **$t_q$  40~100 $\mu$ s**  
 **$I_{TSM}$  62 kA**  
 **$I^2t$  19220 10<sup>3</sup>A<sup>2</sup>S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled, T <sub>c</sub> =55°C	125		4000	4890	A
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	V <sub>DRM</sub> &V <sub>RRM</sub> , tp=10ms V <sub>D</sub> SM&V <sub>R</sub> SM= V <sub>DRM</sub> &V <sub>RRM</sub> +100V	125	2200		3000	V
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	V <sub>D</sub> = V <sub>DRM</sub> V <sub>R</sub> = V <sub>RRM</sub>	125			250	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave	125			62	kA
I <sup>2</sup> t	I <sup>2</sup> T for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>				19220	A <sup>2</sup> s*10 <sup>3</sup>
V <sub>TO</sub>	Threshold voltage		125			1.30	V
r <sub>T</sub>	On-state slop resistance					0.13	mΩ
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =6000A, F=90kN	25			3.00	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> I <sub>TM</sub> to4000A t=5s Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A f=50Hz	125			600	A/μs
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =2000A, tp=1000μs, di/dt=-20A/μs, V <sub>R</sub> =100V	125		2400		μC
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =2000A, tp=1000μs, V <sub>R</sub> =100V dv/dt=30V/μs , di/dt=-20A/μs	125	40		100	μs
I <sub>GT</sub>	Gate trigger current			40		250	mA
V <sub>GT</sub>	Gate trigger voltage	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	0.9		2.5	V
I <sub>H</sub>	Holding current			20		400	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.3	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine double side cooled				0.005	°C /W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink	Clamping force 90 kN				0.0015	
F <sub>m</sub>	Mounting force			81		108	kN
T <sub>stg</sub>	Stored temperature			-40		140	°C
W <sub>t</sub>	Weight				2090/2650		g
Outline	KT110cT/dT						

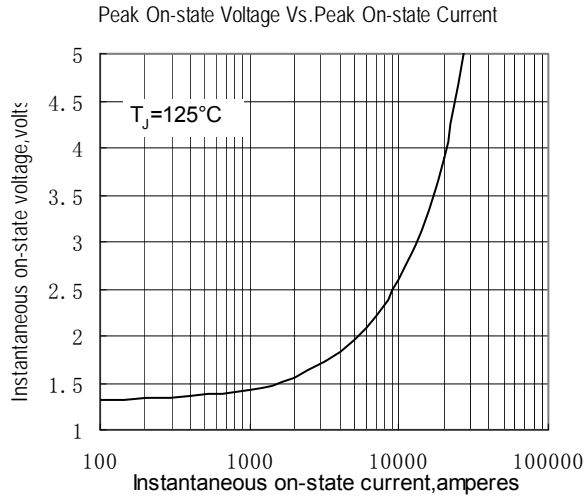


Fig.1

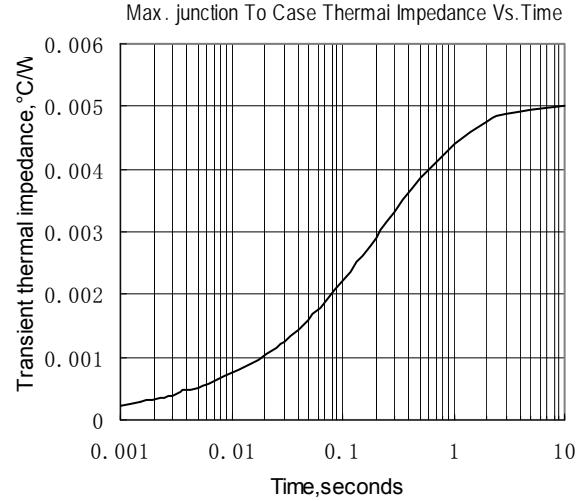


Fig.2

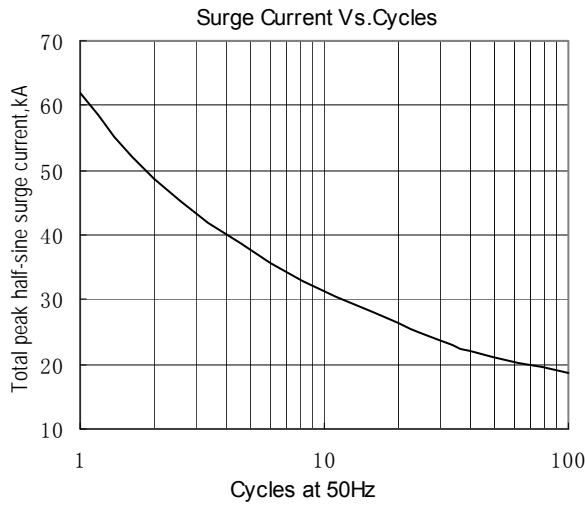


Fig.3

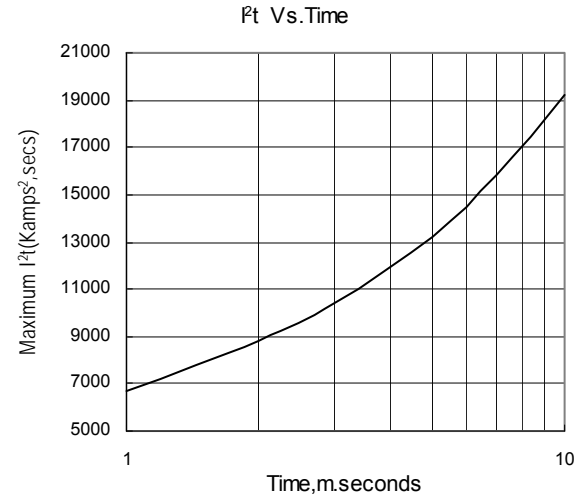


Fig.4

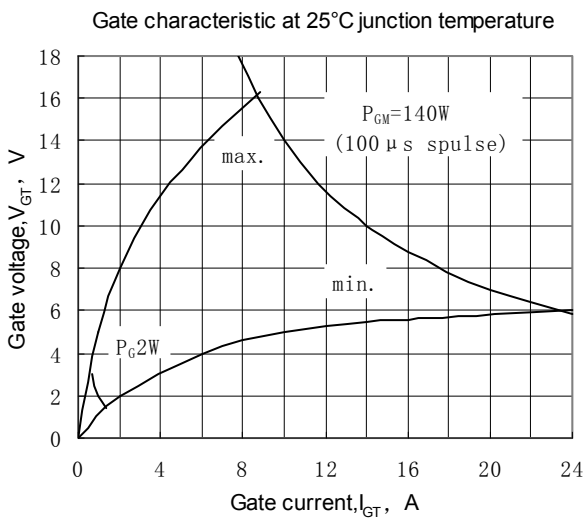


Fig.5

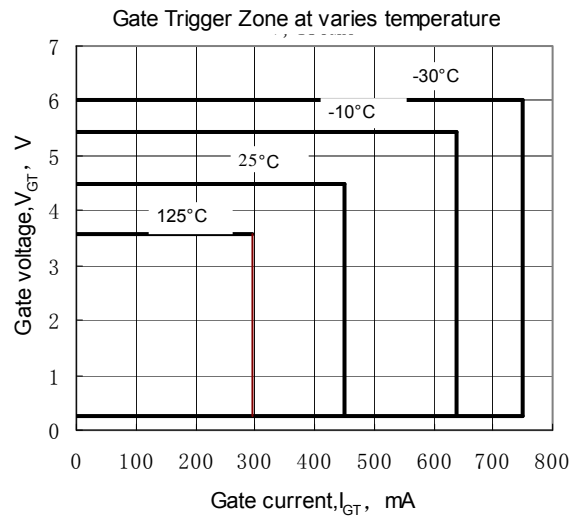


Fig.6



Outline:

图21-KT110cT

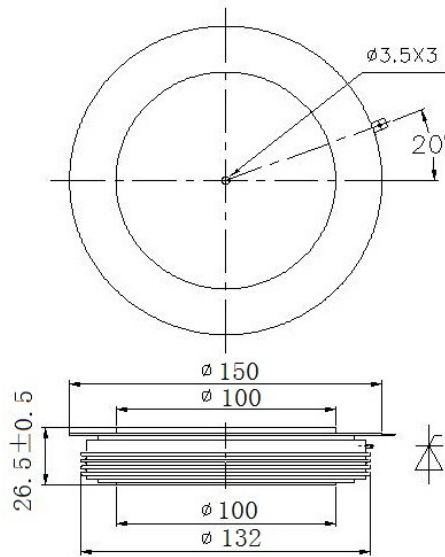
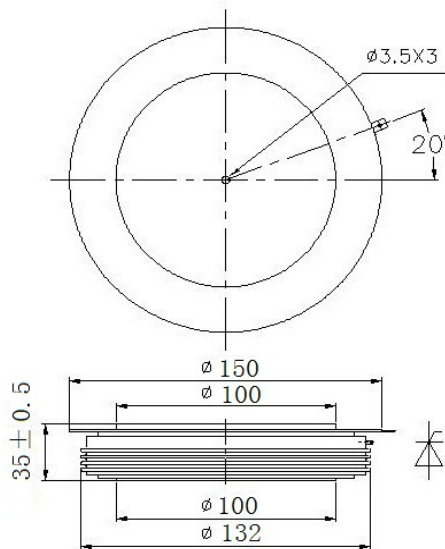


图22-KT110dT



地 址 Address: 辽宁省锦州市滨海新区黔江街21号

邮 编 Zipcode: 121007

电 话 Telephone: 0416-2936666 18840127688

传 真 Fax: 0416-2936888

网 址 Web Sit: <http://www.power-semi.com>

电子邮箱 Email: 13904168481@126.com